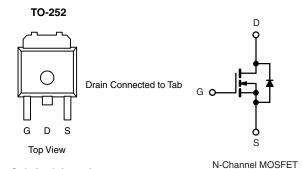




N-Channel 20 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY			
V _{DS} (V)	$R_{DS(on)}\left(\Omega\right)$ I_{D}		
20	0.0043 at V _{GS} = 10 V	34	
	0.006 at V _{GS} = 4.5 V	28	



Ordering Information: SUD50N02-04P-E3 (Lead (Pb)-free)

FEATURES

- TrenchFET® Power MOSFET
- 175 °C Junction Temperature
- PWM Optimized for High Efficiency
- Material categorization: definitions compliance please see www.vishay.com/doc?99912

APPLICATIONS

- Synchronous Buck Converter
 - Low-Side
 - Desktop, Servers, Desknote
- Synchronous Rectification
 - POL

ABSOLUTE MAXIMUM RATINGS $(T_A = 2)$	25 °C, unless othe	rwise noted)			
Parameter	Symbol	Limit	Unit		
Drain-Source Voltage		V _{DS}	20	V	
Gate-Source Voltage		V _{GS}	± 20	1 v	
	T _A = 25 °C	- I _D	34 ^a		
Continuous Drain Current ^a	T _C = 25 °C		50 ^b		
Pulsed Drain Current		I _{DM}	100	Α	
Continuous Source Current (Diode Conduction) ^a	I _S	8.3 ^a			
Avalanche Current ^C	L = 0.1 mH	I _{AS}	50		
Avalanche Energy ^c	L = 0.1 IIII1	E _{AS}	125	mJ	
Maximum Power Dissipation	T _A = 25 °C	P _D	8.3 ^a	w	
Maximum Power Dissipation	T _C = 25 °C	1 'D	136]	
Operating Junction and Storage Temperature Range	•	T _J , T _{stg}	- 55 to 175	°C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Marrian una lumation de Ameliando	t ≤ 10 s	R _{thJA}	15	18	°C/W
Maximum Junction-to-Ambient ^a	Steady State		40	50	
Maximum Junction-to-Case		R _{thJC}	0.85	1.1	

Notes:

- a. Surface mounted on FR4 board, $t \le 10 \text{ s.}$
- b. Limited by package.
- c. Single pulse.

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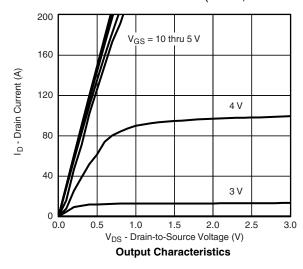
SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)							
Parameter	Symbol	Test Conditions	Min.	Typ. ^a	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V _{(BR)DSS}	$V_{GS} = 0 \text{ V}, I_{D} = 250 \mu\text{A}$	20			V	
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	0.8		3.0	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 20 V, V _{GS} = 0 V			1	μΑ	
	1033	V _{DS} = 20 V, V _{GS} = 0 V, T _J = 125 °C			50		
On-State Drain Current ^b	I _{D(on)}	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	50			Α	
Drain-Source On-State Resistance ^b		$V_{GS} = 10 \text{ V}, I_D = 20 \text{ A}$		0.0035	0.0043		
	R _{DS(on)}	$V_{GS} = 10 \text{ V}, I_D = 20 \text{ A}, T_J = 125 ^{\circ}\text{C}$			0.0061	Ω	
		$V_{GS} = 4.5 \text{ V}, I_D = 20 \text{ A}$		0.0048	0.006		
Forward Transconductance ^b	9 _{fs}	$V_{DS} = 15 \text{ V}, I_D = 20 \text{ A}$	15			S	
Dynamic ^a							
Input Capacitance	C _{iss}			5000		pF	
Output Capacitance	C _{oss}	$V_{GS} = 0 \text{ V}, V_{DS} = 10 \text{ V}, f = 1 \text{ MHz}$		1650			
Reverse Transfer Capacitance	C _{rss}			770			
Gate Resistance	R_g	f = 1 MHz		1.6		Ω	
Total Gate Charge ^c	Q_g			40	60		
Gate-Source Charge ^c	Q_{gs}	$V_{DS} = 10 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 50 \text{ A}$		14		nC	
Gate-Drain Charge ^c	Q _{gd}			13			
Turn-On Delay Time ^c	t _{d(on)}			20	30		
Rise Time ^c	t _r	$V_{DD} = 10 \text{ V}, R_{L} = 0.2 \Omega$		20	30	ns	
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong 50 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 2.5 \Omega$		50	75		
Fall Time ^c	t _f			15	25		
Source-Drain Diode Ratings and Cha	racteristics	T _C = 25 °C					
Pulsed Current	I _{SM}				100	Α	
Diode Forward Voltage ^b	V_{SD}	$I_F = 50 \text{ A}, V_{GS} = 0 \text{ V}$		0.9	1.5	V	
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 50 A, dI/dt = 100 A/μs		45	70	ns	

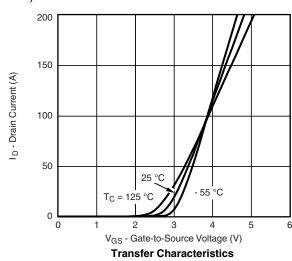
Notes:

- a. Guaranteed by design, not subject to production testing.
- b. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

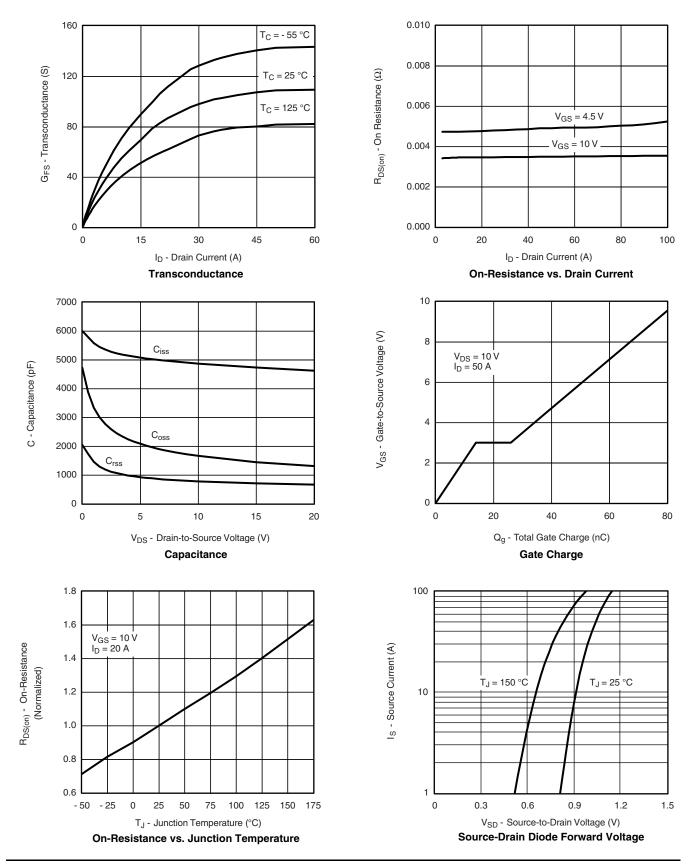




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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



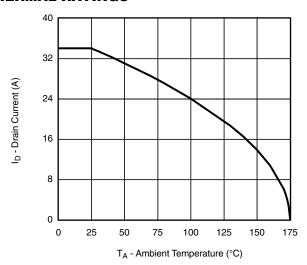
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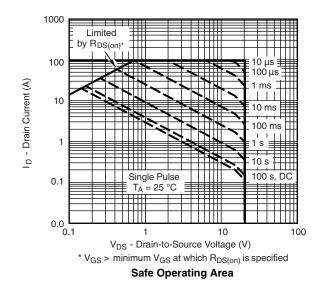
THERMAL RATINGS

2

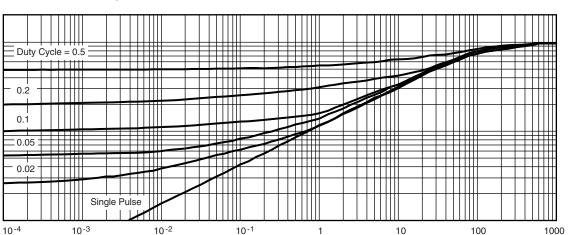
0.01

Normalized Effective Transient Thermal Impedance





Max. Avalanche and Drain Current vs. **Ambient Temperature**



Square Wave Pulse Duration (s) Normalized Thermal Transient Impedance, Junction-to-Ambient

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